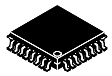


HIGH EFFICIENCY CLASS-G ADSL LINE DRIVER

FEATURES

- **Low Total Power Consumption Increases ADSL Line Card Density (20 dBm on Line)**
  - **600 mW w/Active Termination (Full Bias)**
  - **530 mW w/Active Termination (Low Bias)**
- **Low MTPR of –74 dBc (All Bias Conditions)**
- **High Output Current of 500 mA (typ)**
- **Wide Supply Voltage Range of ±5 V to ±15 V [$V_{CC(H)}$] and ±3.3 V to ±15 V [$V_{CC(L)}$]**
- **Wide Output Voltage Swing of 43 Vpp Into 100-Ω Differential Load [$V_{CC(H)} = \pm 12$ V]**
- **Multiple Bias Modes Allow Low Quiescent Power Consumption for Short Line Lengths**
  - **160-mW/ch Full Bias Mode**
  - **135-mW/ch Mid Bias Mode**
  - **110-mW/ch Low Bias Mode**
  - **75-mW/ch Terminate Only Mode**
  - **13-mW/ch Shutdown Mode**
- **Low Noise for Increased Receiver Sensitivity**
  - **3.3 $\mathrm{pA}/\sqrt{\mathrm{Hz}}$ Noninverting Current Noise**
  - **9.5 $\mathrm{pA}/\sqrt{\mathrm{Hz}}$ Inverting Current Noise**
  - **3.5 $\mathrm{nV}/\sqrt{\mathrm{Hz}}$ Voltage Noise**

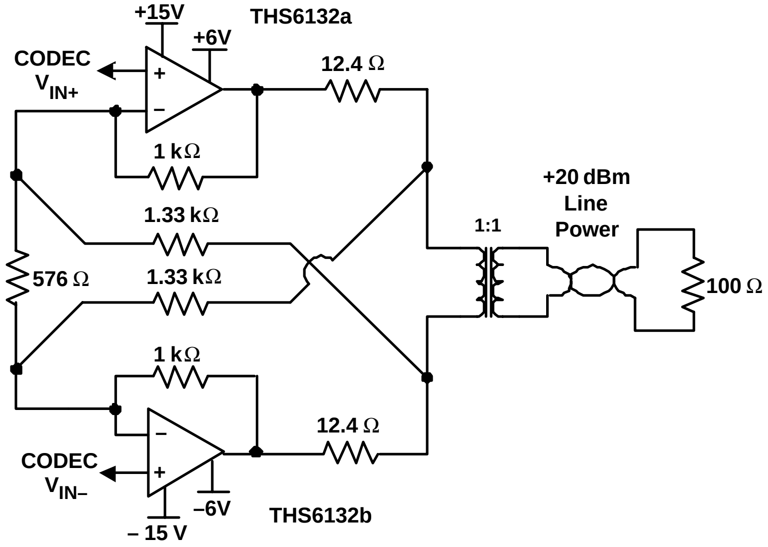
APPLICATIONS

- **Ideal for Active Termination Full Rate ADSL DMT applications (20-dBm Line Power)**

DESCRIPTION

The THS6132 is a Class-G current feedback differential line driver ideal for full rate ADSL DMT systems. Its extremely low power consumption of 600 mW or lower is ideal for ADSL systems that must achieve high densities in ADSL central office rack applications. The unique patent pending architecture of the THS6132 allows the quiescent current to be much lower than existing line drivers while still achieving very high linearity. In addition, the multiple bias settings of the amplifiers allow for even lower power consumption for line lengths where the full performance of the amplifier is not required. The output voltage swing has been vastly improved over first generation Glass-G amplifiers and allows the use of lower power supply voltages that help conserve power. For maximum flexibility, the THS6132 can be configured in classical Class-AB mode requiring only as few as one power supply.

Typical ADSL CO Line Driver Circuit Utilizing Active Impedance Supporting A 6.3 Crest Factor



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage.

ORDERING INFORMATION

PRODUCT	PACKAGE	PACKAGE CODE	SYMBOL	T_A	ORDER NUMBER	TRANSPORT MEDIA
THS6132VFP	TQFP-32 PowerPAD™	VFP–32	THS6132	–40°C to 85°C	THS6132VFP	Tube
					THS6132VFPR	Tape and reel
THS6132RGW	Leadless 25-pin 5,mm x 5, mm PowerPAD™	RGW–25	6132		THS6132RGWR	Tape and reel

PACKAGE DISSIPATION RATINGS

PACKAGE	Θ_{JA}	Θ_{JC}	$T_A \leq 25°C$ POWER RATING(1)	$T_A = 70°C$ POWER RATING(1)	$T_A = 85°C$ POWER RATING(1)
VFP–32	29.4°C/W	0.96°C/W	3.57 W	2.04 W	1.53 W
RGW–25	31°C/W	1.7°C/W	3.39 W	1.94 W	1.45 W

(1) Power rating is determined with a junction temperature of 130°C. This is the point where distortion starts to substantially increase. Thermal management of the final PCB should strive to keep the junction temperature at or below 125°C for best performance.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

		THS6132
Supply voltage, $V_{CC(H)}$ and $V_{CC(L)}$ (2)		±16.5 V
Input voltage, V_I		$\pm V_{CC(L)}$
Output current, I_O (3)		900 mA
Differential input voltage, V_{IO}		±2 V
Maximum junction temperature, T_J (see Dissipation Rating Table for more information)		150°C
Operating free–air temperature, T_A		–40°C to 85°C
Storage temperature, T_{Stg}		65°C to 150°C
Lead temperature, 1,6 mm (1/16–inch) from case for 10 seconds		300°C
ESD ratings	HBM	1 kV
	CDM	500 V
	MM	200 V

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) $V_{CC(H)}$ must always be greater than or equal to $V_{CC(L)}$ for proper operation. Class-AB mode operation occurs when $V_{CC(H)}$ is equal to VCC(L) and is considered acceptable operation for the THS6132 even though it is not fully specified in this mode of operation.

(3) The THS6132 incorporates a PowerPAD on the underside of the chip. This acts as a heatsink and must be connected to a thermally dissipating plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature that could permanently damage the device. See TI Technical Brief SLMA002 for more information about utilizing the PowerPAD thermally enhanced package.

PowerPAD is a trademark of Texas Instruments.

RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
Supply voltage	$+V_{CC(H)}$ to $-V_{CC(H)}$	$\pm V_{CC(L)}$	±15	±16	V
	$+V_{CC(L)}$ to $-V_{CC(L)}$	±3.3	±5	$\pm V_{CC(H)}$	
Operating free-air temperature, T_A		–40		85	°C

ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range, T_A = 25°C, $V_{CC(H)}$ = ±15 V, $V_{CC(L)}$ = ±5 V R_F = 1.5 kΩ, Gain = +10, Full Bias Mode, R_L = 50 Ω (unless otherwise noted)

	PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
NOISE/DISTORTION PERFORMANCE								
	Multitone power ratio		Gain =+11, 163kHz to 1.1MHz DMT, +20 dBm Line Power, 1:1.1 transformer, active termination, synthesis factor = 4			–74		dBc
	Receive band spill-over		Gain =+11, 25 kHz to 138 kHz with MTPR signal applied			–95		dBc
HD	Harmonic distortion (Differential Configuration, f = 1 MHz, $V_{O(PP)}$ = 2 V, Gain = +10)		2nd harmonic	Differential load = 100 Ω		–84		dBc
				Differential load = 25 Ω		–69		
			3rd harmonic	Differential load = 100 Ω		–92		dBc
				Differential load = 25 Ω		–73		
V_n	Input voltage noise		f = 10 kHz			3.5		$nV/\sqrt{Hz}$
I_n	Input current noise	+Input	f = 10 kHz			3.3		$pA/\sqrt{Hz}$
		–Input				9.5		
	Crosstalk		f = 1 MHz, R_L = 100 Ω,	$V_{O(PP)}$ = 2 V, Gain = +2		–52		dBc
OUTPUT CHARACTERISTICS								
V_O	Single–ended output voltage swing		$V_{CC(H)}$ = ±12 V	R_L = 100 Ω	±10.4	±10.8		V
				R_L = 30 Ω	±9.9	±10.4		
			$V_{CC(H)}$ = ±15 V	R_L = 100 Ω	±13.3	±13.8		V
				R_L = 50 Ω	±13	±13.6		
	Output voltage transition from $V_{CC(L)}$ to $V_{CC(H)}$ (Point where $I_{CC(L)} = I_{CC(H)}$)		R_L = 50 Ω	$V_{CC(L)}$ = ±5 V		±3.1		V
				$V_{CC(L)}$ = ±6 V		±3.9		
I_O	Output current (1)		R_L = 10 Ω	$V_{CC(H)}$ = ±12 V		±500		mA
				$V_{CC(H)}$ = ±15 V	±400	±500		
$I_{(SC)}$	Short-circuit current (1)		R_L = 1 Ω	$V_{CC(H)}$ = ±15 V		±750		mA
	Output resistance		Open-loop			5		Ω
	Output resistance—terminate mode		f = 1 MHz,	Gain = +10		0.35		Ω
	Output resistance—shutdown mode		f = 1 MHz,	Open-loop		5.5		kΩ

(1) A heatsink is required to keep the junction temperature below absolute maximum rating when an output is heavily loaded or shorted. See Absolute Maximum Ratings section for more information.

ELECTRICAL CHARACTERISTICS (continued)

over recommended operating free-air temperature range, T_A = 25°C, $V_{CC(H)}$ = ±15 V, $V_{CC(L)}$ = ±5 V R_F = 1.5 kΩ, Gain = +10, Full Bias Mode, R_L = 50 Ω (unless otherwise noted)

POWER SUPPLY							
PARAMETER		**TEST CONDITIONS**		**MIN**	**TYP**	**MAX**	**UNIT**
$V_{CC(x)}$	Operating range	±$V_{CC(H)}$		±$V_{CC(L)}$	±15	±16.5	V
		±$V_{CC(L)}$		±3	±5	±$V_{CC(H)}$	
I_{CC}	Quiescent current (each driver) Full-bias mode (Bias–1 = 1, Bias–2 = 1, Bias–3 = X) (Icc trimmed with $V_{CC(H)}$ = ±15 V, $V_{CC(L)}$ = ±5 V)	$V_{CC(L)}$ = ±5 V; ($V_{CC(H)}$= ±15 V)	T_A = 25°C	5.7	6.4	7.5	mA
			T_A = full range			8.1	
		$V_{CC(L)}$ = ±6 V; ($V_{CC(H)}$ = ±15 V)	T_A = 25°C		6.7		mA
			T_A = full range				
		$V_{CC(H)}$ = ±12 V; ($V_{CC(L)}$ = ±5 V)	T_A = 25°C		3.1		mA
			T_A = full range				
		$V_{CC(H)}$ = ±15 V; ($V_{CC(L)}$ = ±5 V)	T_A = 25°C	2.9	3.25	3.75	mA
			T_A = full range			4.25	
	Quiescent current (each driver) Variable bias modes, $V_{CC(L)}$ = ±5 V	Mid; Bias–1 = 1, Bias–2 = 0, Bias–3 = 1		5.0	5.6	6.8	mA
		Low; Bias–1 = 1, Bias–2 = 0, Bias–3 = 0		4.25	4.8	6.0	
		Terminate; Bias–1 = 0, Bias–2 = 1, Bias–3 = X(1)		3.2	3.8	4.5	
		Shutdown; Bias–1 = 0, Bias–2 = 0, Bias–3 = X(1)			1	1.3	
	Quiescent current (each driver) Variable bias modes, $V_{CC(H)}$ = ±15 V	Mid; Bias–1 = 1, Bias–2 = 0, Bias–3 = 1		2.4	2.7	3.0	mA
		Low ; Bias–1 = 1, Bias–2 = 0, Bias–3 = 0		1.9	2.15	2.4	
		Terminate; Bias–1 = 0, Bias–2 = 1, Bias–3 = X(1)		1.1	1.3	1.5	
		Shutdown ; Bias–1 = 0, Bias–2 = 0, Bias–3 = X(1)			0.1	0.5	
PSRR	Power supply rejection ratio ($\Delta V_{CC(x)}$ = ±1 V)	$V_{CC(L)}$ = ±5V	T_A = 25°C	–70	–82		dB
			T_A = full range	–68			
		$V_{CC(H)}$ = ±15V	T_A = 25°C	–70	–82		
			T_A = full range	–68			

(1) X is used to denote a logic state of either 1 or 0.

ELECTRICAL CHARACTERISTICS (continued)

over recommended operating free-air temperature range, T_A = 25°C, $V_{CC(H)}$ = ±15 V, $V_{CC(L)}$ = ±5 V R_F = 1.5 kΩ, Gain = +10, Full Bias Mode, R_L = 50 Ω (unless otherwise noted)

DYNAMIC PERFORMANCE							
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
BW	Single-ended small-signal bandwidth (–3 dB), V_O = 0.1 Vrms	R_L = 100 Ω	Gain = +1, RF = 750 Ω		80		MHz
			Gain = +2, RF = 620 Ω		70		
			Gain = +5, RF = 500 Ω		60		
			Gain = +10, RF = 1 kΩ		20		
		R_L = 25 Ω	Gain = +1, RF = 750 Ω		60		MHz
			Gain = +2, RF = 620 Ω		55		
			Gain = +5, RF = 500 Ω		50		
			Gain = +10, RF = 1 kΩ		17		
SR	Single-ended slew-rate(1)	V_O = 20 V_{PP},	Gain = +10		300		V/µs

(1) Slew-rate is defined from the 25% to the 75% output levels

DC PERFORMANCE							
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OS}	Input offset voltage	$V_{CC(L)}$ = ± 5 V, ±6 V	T_A = 25°C		1	15	mV
			T_A = full range			20	
	Differential offset voltage		T_A = 25°C		0.3	6	
			T_A = full range			8	
	Offset drift		T_A = full range		40		µV/°C
I_{IB}	–Input bias current	$V_{CC(L)}$ = ±5 V, ±6 V	T_A = 25°C		1	15	µA
			T_A = full range			20	
	+ Input bias current		T_A = 25°C		1.5	15	
			T_A = full range			20	
Z_{OL}	Open loop transimpedance	R_L = 1 kΩ			2		MΩ

ELECTRICAL CHARACTERISTICS (continued)

over recommended operating free-air temperature range, T_A = 25°C,$V_{CC(H)}$ = ±15 V, $V_{CC(L)}$ = ±5 V R_F = 1.5 kΩ, Gain = +10, Full Bias Mode, R_L = 50 Ω (unless otherwise noted)

INPUT CHARACTERISTICS

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{ICR}	Input common–mode voltage range(1)	$V_{CC(L)}$ = ±5 V	T_A = 25°C	±2.7	±3.0		V
			T_A = full range	±2.6			
		$V_{CC(L)}$ = ±6 V	T_A = 25°C		±4.0		
	REF pin input voltage range	$V_{CC–(L)}$= ±5 V			±2.5		V
		$V_{CC(L)}$ = ±6 V			±3.5		
CMRR	Common-mode rejection ratio	$V_{CC(L)}$ = ±5 V, ±6 V	T_A = 25°C	60	67		dB
			T_A = full range	57			
R_I	Input resistance	+ Input			800		kΩ
		– Input			45		Ω
C_I	Differential Input capacitance				1.2		pF

(1) To conserve as much power as possible, the input stage of the THS6132 is powered from the $V_{CC(L)}$ supplies and is limited by the $V_{CC(L)}$ supply voltage. For Class-AB operation, connect the $V_{CC(L)}$ supplies to $V_{CC(H)}$.

LOGIC CONTROL CHARACTERISTICS

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IH}	Bias pin voltage for logic 1	Relative to DGND pin voltage	2.0			V
V_{IL}	Bias pin voltage for logic 0	Relative to DGND pin voltage			0.8	V
I_{IH}	Bias pin current for logic 1	V_{IH} = 5 V, DGND = 0 V		–0.1	–0.2	µA
I_{IL}	Bias pin current for logic 0	V_{IL} = 0 V, DGND = 0 V		–0.1	–0.2	µA
	Transition time—logic 0 to logic 1(1)			0.1		µs
	Transition time—logic 1 to logic 0(1)			0.2		µs
	DGND useable range		$–V_{CC(H)}$		$+V_{CC(H)}$ –5	V

(1) Transition time is defined as the time from when the logic signal is applied to the time when the supply current has reached half its final value.

LOGIC TABLE

BIAS-1	BIAS-2	BIAS-3	FUNCTION	DESCRIPTION
1	1	X(1)	Full bias mode	Amplifiers ON with lowest distortion possible
1	0	1	Mid bias mode	Amplifiers ON with power savings with a reduction in distortion performance
1	0	0	Low bias mode	Amplifiers ON with enhanced power savings and a reduction of distortion performance
0	1	X(1)	Terminate mode	Lowest power state with +Vin pins internally connect to REF pin and output has low impedance
0	0	X(1)	Shutdown mode	Amplifiers OFF and output has high impedance

(1) X is used to denote a logic state of either 1 or 0.

NOTE: The default state for all logic pins is a logic one (1).

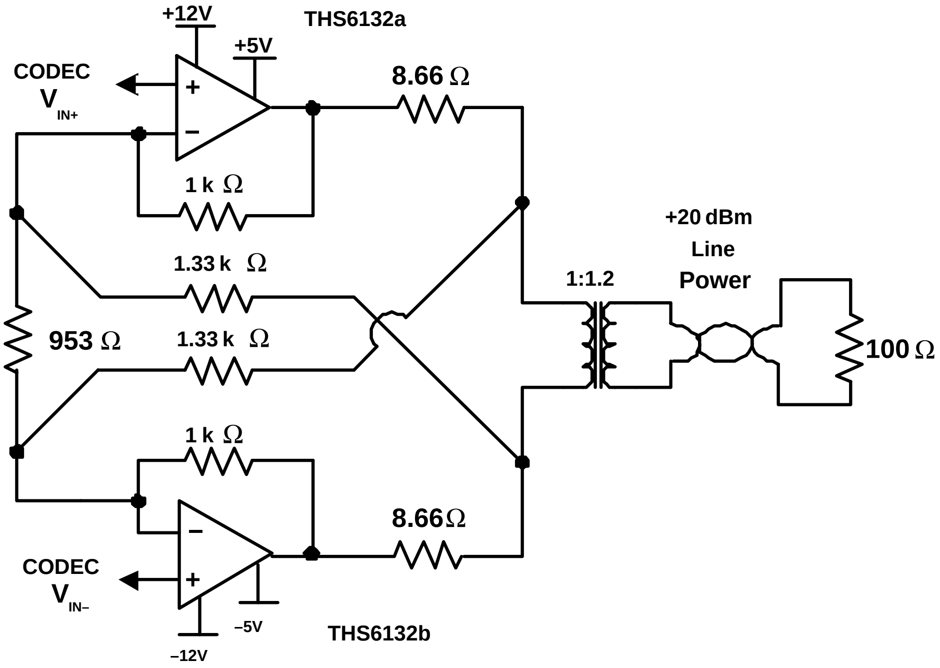
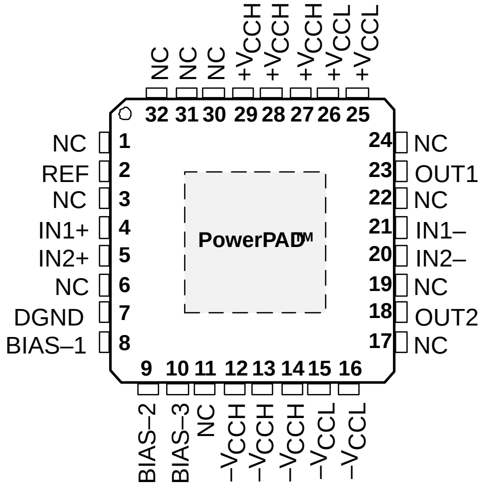


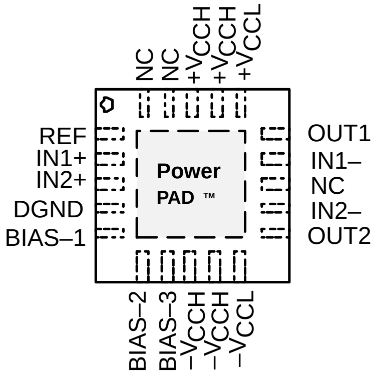
Figure 1. ±12 V Active Termination ADSL CO Line Driver Circuit (Synthesis Factor = 4; CF = 5.6)

PIN ASSIGNMENTS

THS6132
TQFP PowerPAD (VFP) PACKAGE
(TOP VIEW)



THS6132
Leadless 5X5 PowerPAD
(RGW) PACKAGE
(TOP VIEW)



TYPICAL CHARACTERISTICS

Table of Graphs

		FIGURE
Output voltage headroom	vs Output current	2
Common-mode rejection ratio	vs Frequency	3
Crosstalk	vs Frequency	4
Quiescent current	vs Temperature	5, 6
Large signal bandwidth	vs Frequency	7 – 10
Noise	vs Frequency	11
Overdrive recovery		12
Power supply rejection ratio	vs Frequency	13
Small signal frequency response		14, 15, 16
Small signal bandwidth	vs Frequency	17 – 28
Slew rate	vs Output voltage	29
Closed-loop output impedance	vs Frequency	30, 31
Shutdown response		32
Common-mode rejection ratio	vs Common-mode input voltage	33
Input bias current	vs Temperature	34
Input offset voltage	vs Temperature	35
Current draw distribution	vs Output voltage	36, 37
Output voltage	vs Temperature	38
Differential distortion	vs Frequency	39 – 52
Differential distortion	vs Differential output voltage	53 – 63
Single ended distortion	vs Frequency	64, 65

OUTPUT VOLTAGE HEADROOM
vs
OUTPUT CURRENT

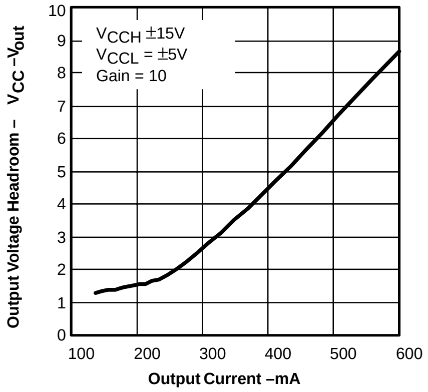


Figure 2

COMMON-MODE REJECTION RATIO
vs
FREQUENCY

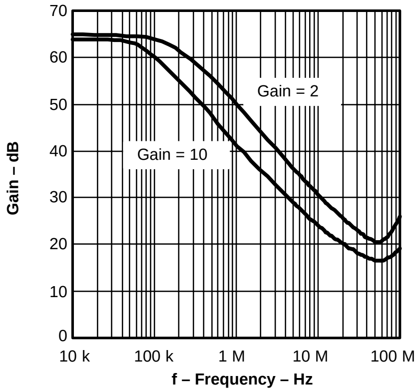


Figure 3

CROSSTALK
vs
FREQUENCY

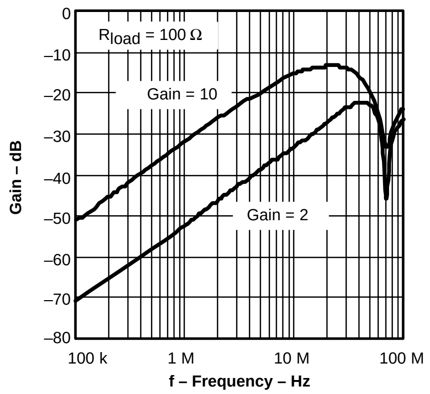


Figure 4

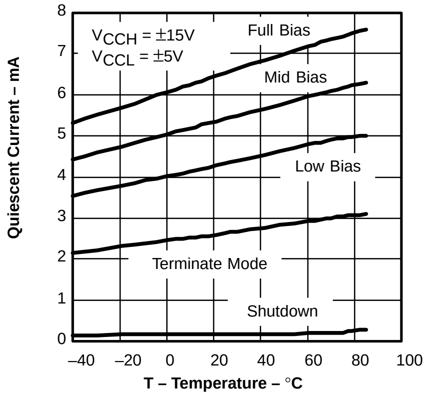

QUIESCENT CURRENT vs TEMPERATURE

Figure 5

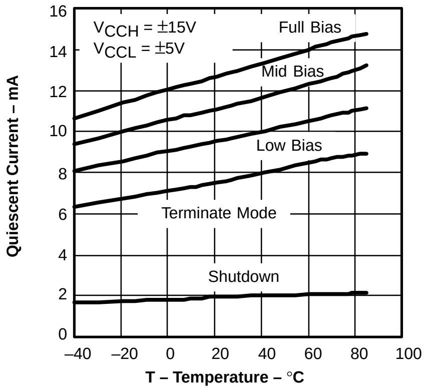

QUIESCENT CURRENT vs TEMPERATURE

Figure 6

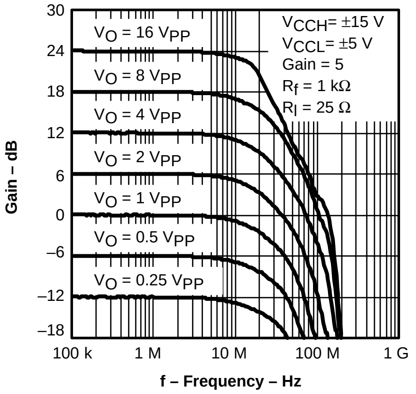

LARGE SIGNAL BANDWIDTH vs FREQUENCY

Figure 7

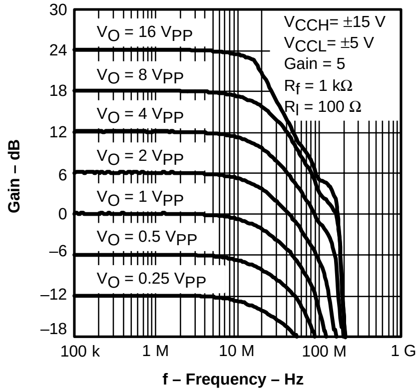

LARGE SIGNAL BANDWIDTH vs FREQUENCY

Figure 8

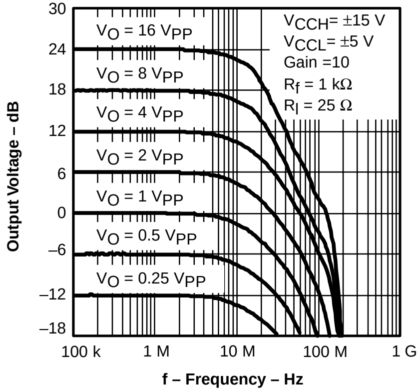

LARGE SIGNAL BANDWIDTH vs FREQUENCY

Figure 9

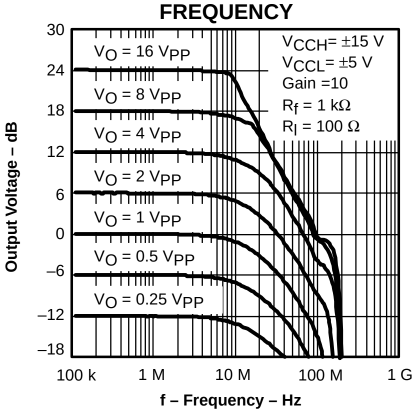

LARGE SIGNAL BANDWIDTH vs FREQUENCY

Figure 10

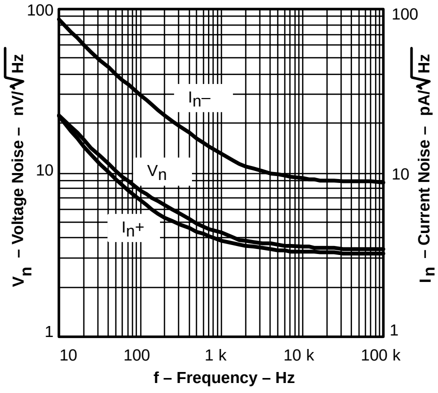

NOISE vs FREQUENCY

Figure 11

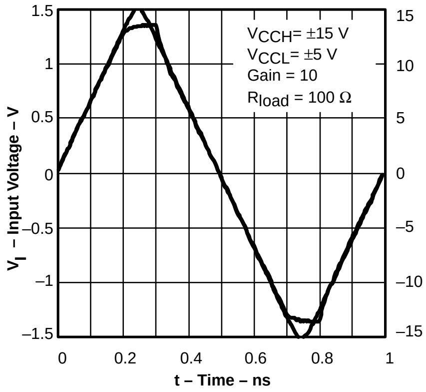

OVERDRIVE RECOVERY

Figure 12

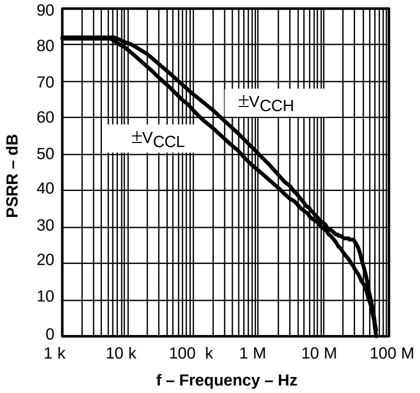

POWER SUPPLY REJECTION RATIO vs FREQUENCY

Figure 13

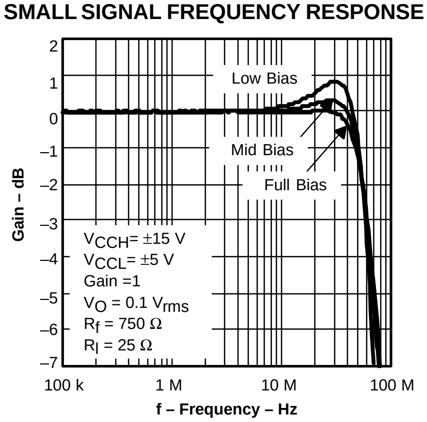


Figure 14

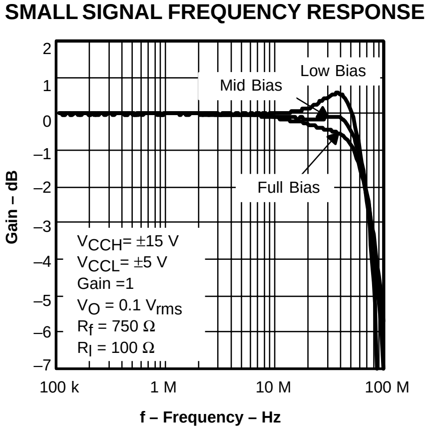


Figure 15

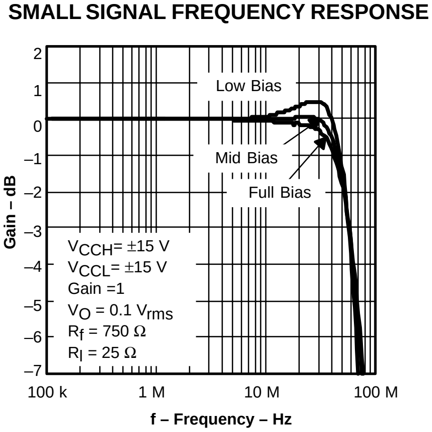


Figure 16

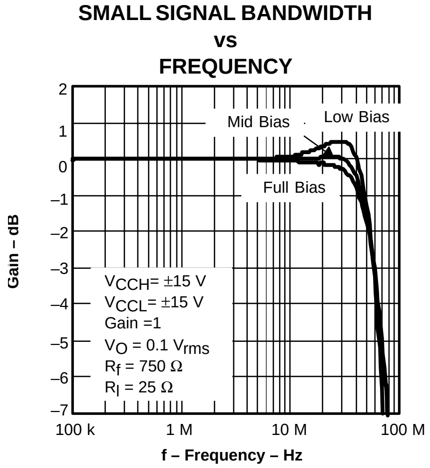


Figure 17

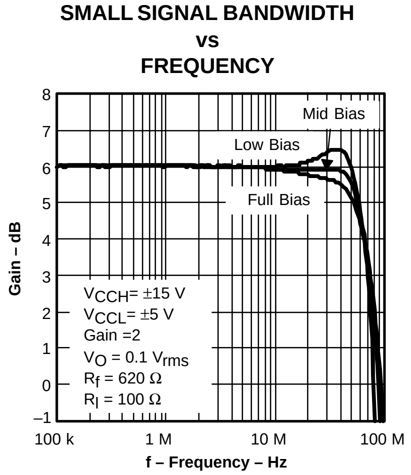


Figure 18

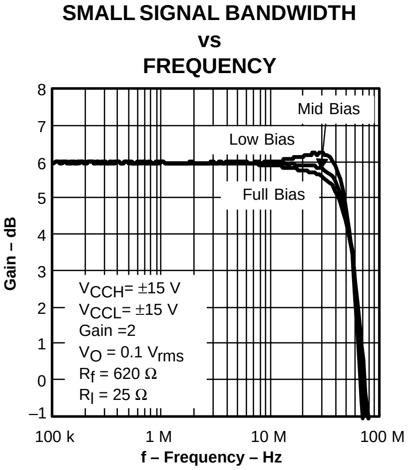


Figure 19

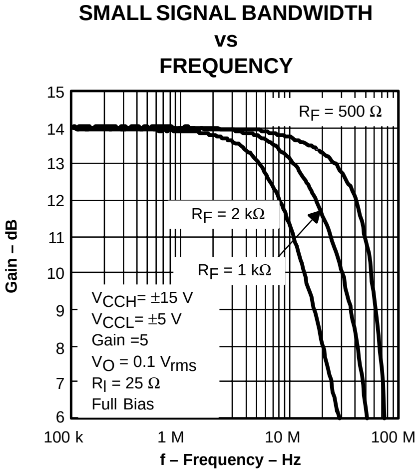


Figure 20

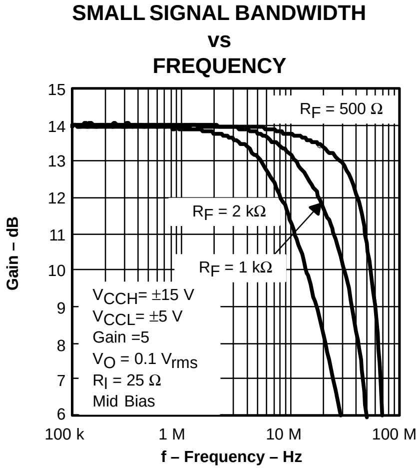


Figure 21

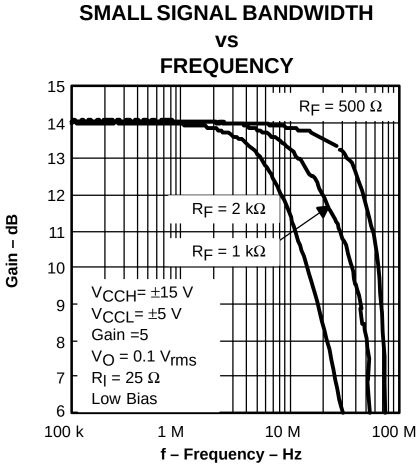


Figure 22

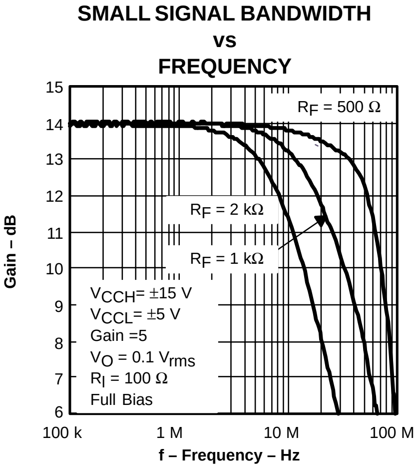

SMALL SIGNAL BANDWIDTH vs FREQUENCY

Figure 23

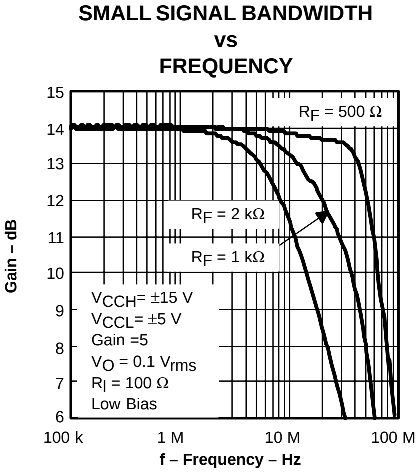

SMALL SIGNAL BANDWIDTH vs FREQUENCY

Figure 24

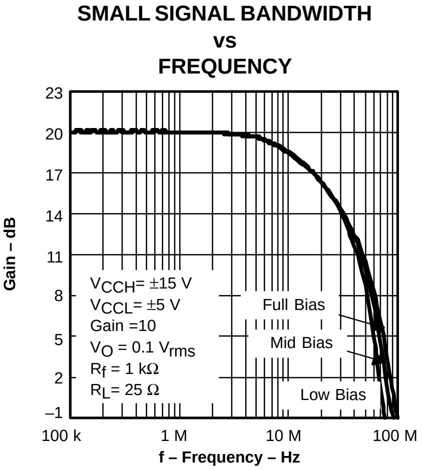

SMALL SIGNAL BANDWIDTH vs FREQUENCY

Figure 25

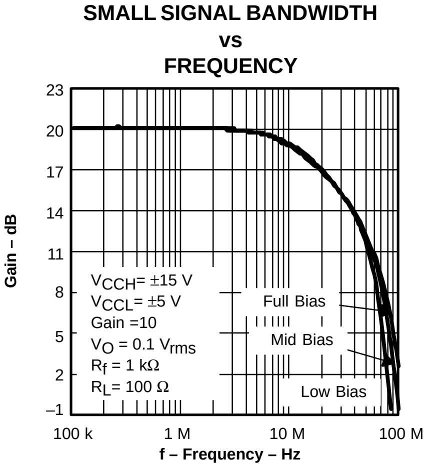

SMALL SIGNAL BANDWIDTH vs FREQUENCY

Figure 26

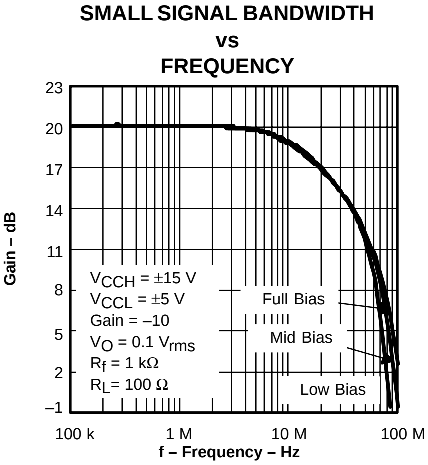

SMALL SIGNAL BANDWIDTH vs FREQUENCY

Figure 27

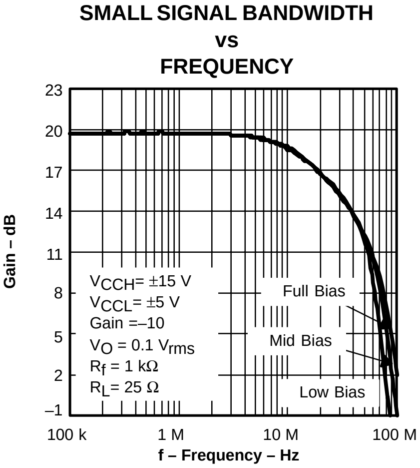

SMALL SIGNAL BANDWIDTH vs FREQUENCY

Figure 28

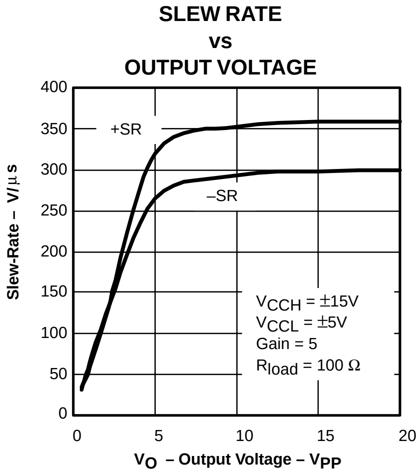

SLEW RATE vs OUTPUT VOLTAGE

Figure 29

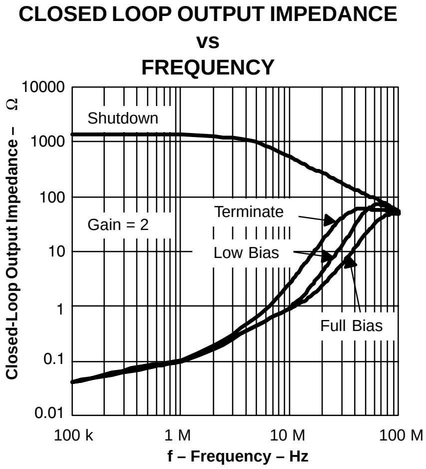

CLOSED LOOP OUTPUT IMPEDANCE vs FREQUENCY

Figure 30

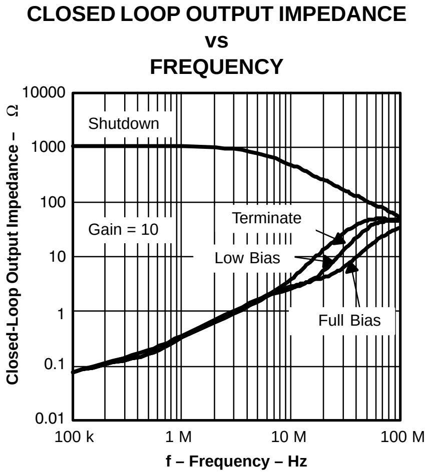

CLOSED LOOP OUTPUT IMPEDANCE vs FREQUENCY

Figure 31

SHUTDOWN RESPONSE

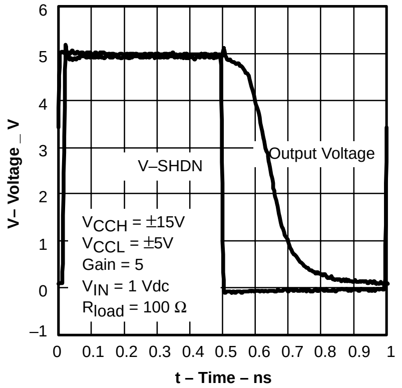


Figure 32

COMMON-MODE REJECTION RATIO vs COMMON-MODE INPUT VOLTAGE

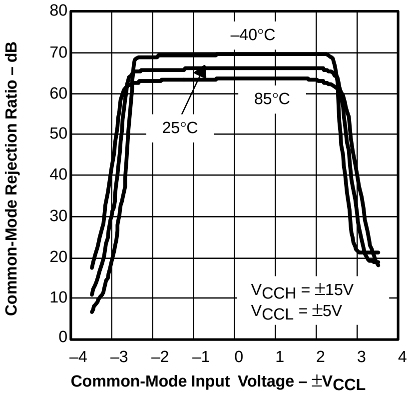


Figure 33

INPUT BIAS CURRENT vs TEMPERATURE

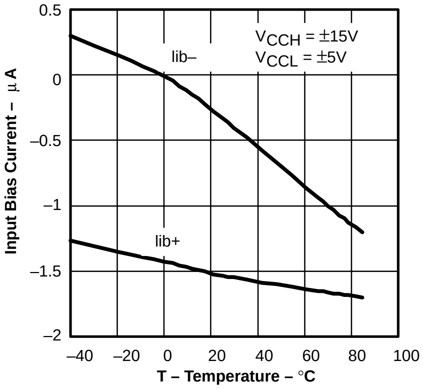


Figure 34

INPUT OFFSET VOLTAGE vs TEMPERATURE

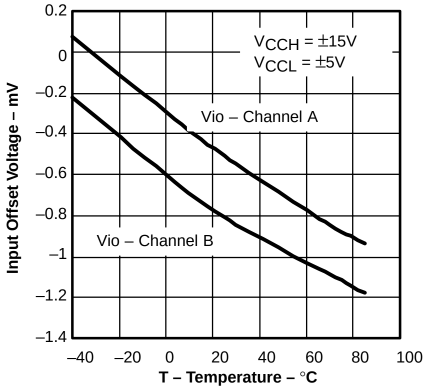


Figure 35

CURRENT DRAW DISTRIBUTION vs OUTPUT VOLTAGE

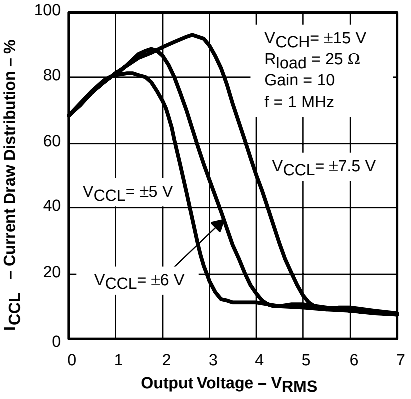


Figure 36

CURRENT DRAW DISTRIBUTION vs OUTPUT VOLTAGE

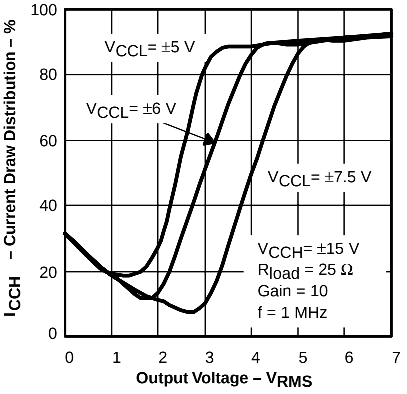


Figure 37

OUTPUT VOLTAGE vs TEMPERATURE

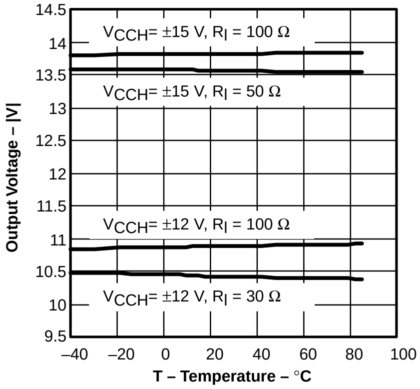


Figure 38

DIFFERENTIAL DISTORTION vs FREQUENCY

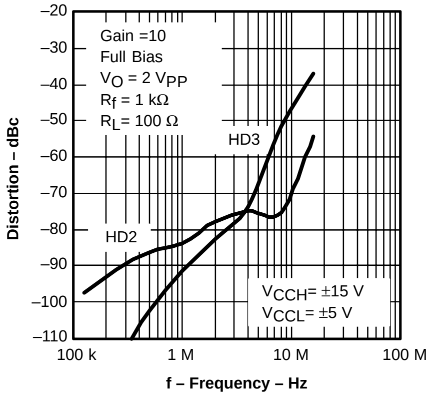


Figure 39

DIFFERENTIAL DISTORTION vs FREQUENCY

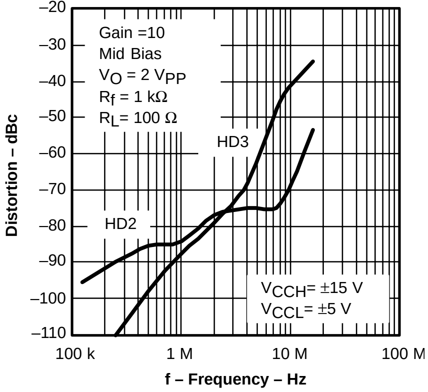


Figure 40

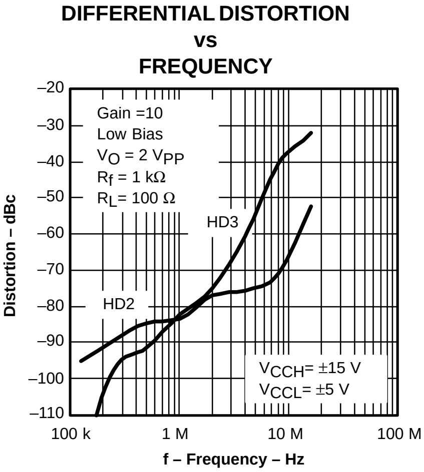

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 41

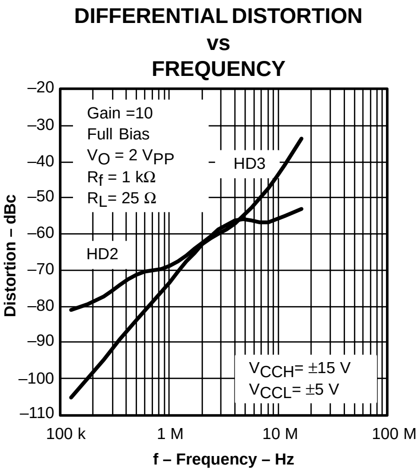

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 42

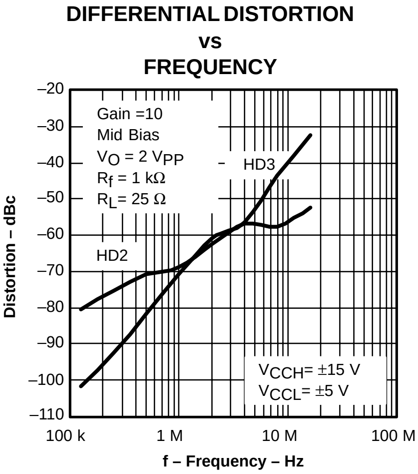

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 43

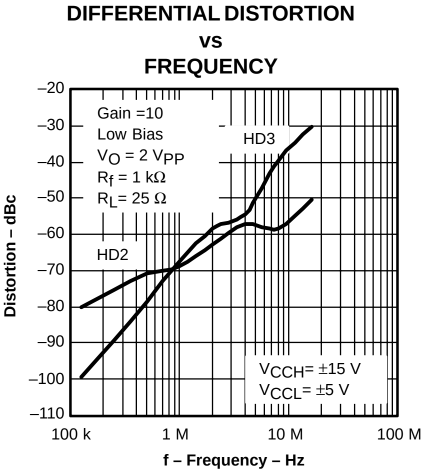

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 44

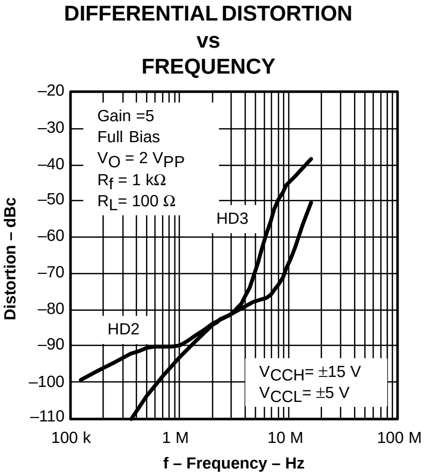

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 45

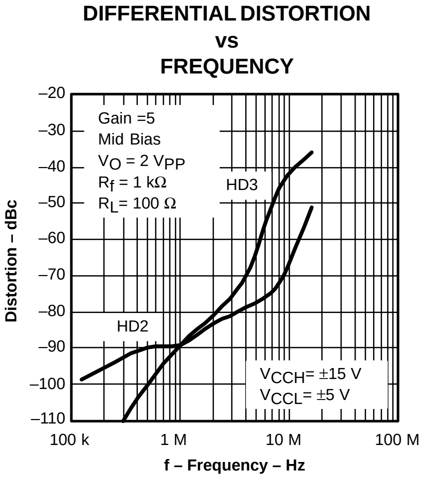

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 46

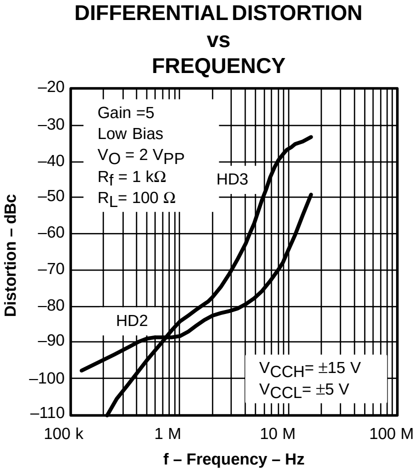

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 47

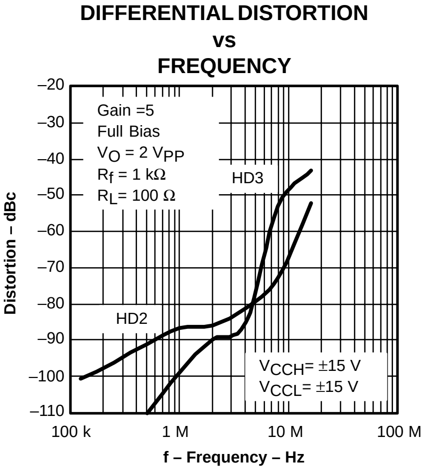

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 48

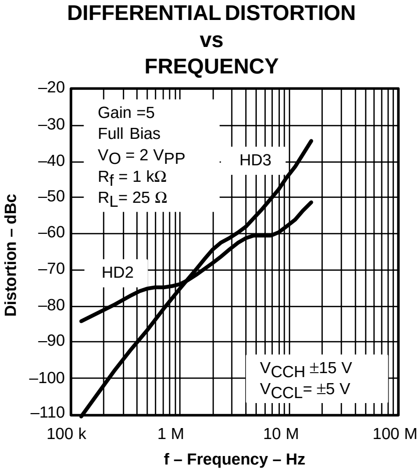

DIFFERENTIAL DISTORTION vs FREQUENCY

Figure 49

DIFFERENTIAL DISTORTION
vs
FREQUENCY

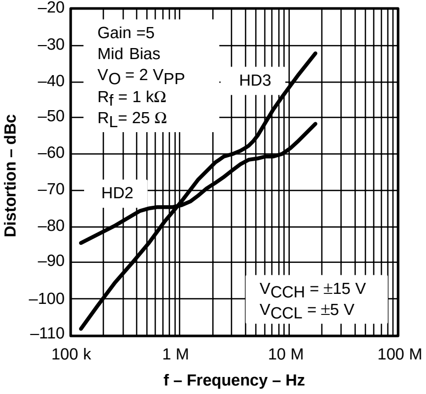


Figure 50

DIFFERENTIAL DISTORTION
vs
FREQUENCY

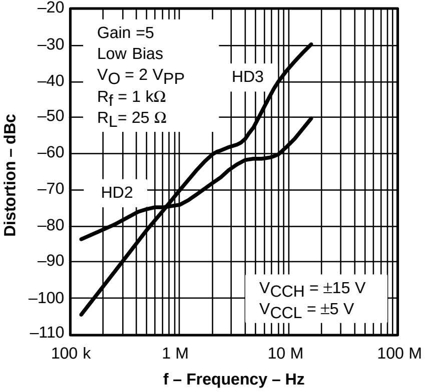


Figure 51

DIFFERENTIAL DISTORTION
vs
FREQUENCY

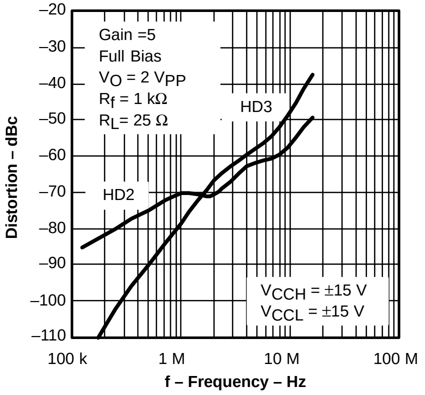


Figure 52

DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE

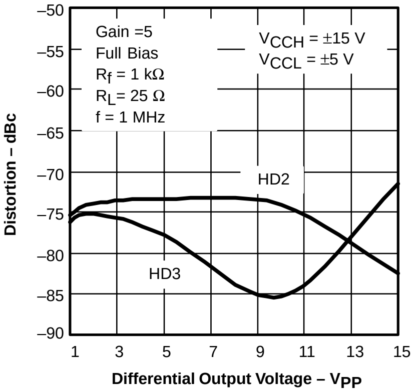


Figure 53

DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE

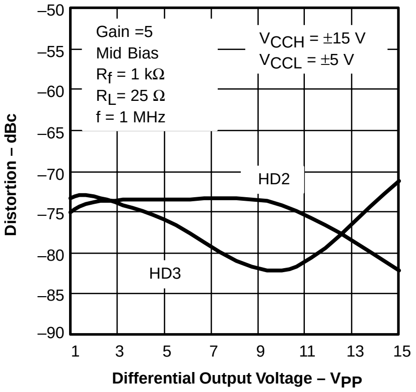


Figure 54

DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE

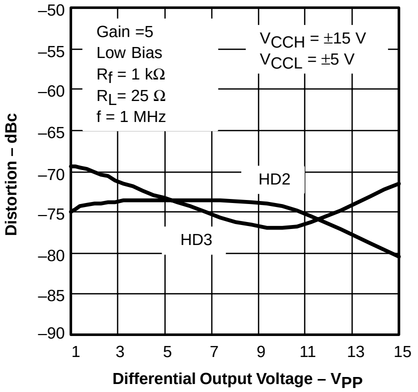


Figure 55

DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE

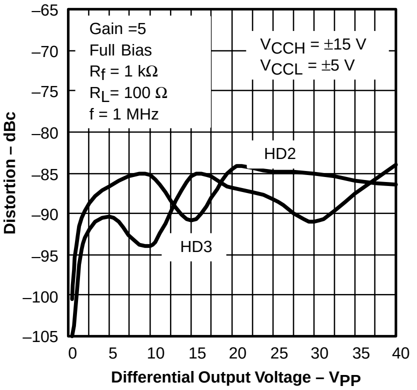


Figure 56

DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE

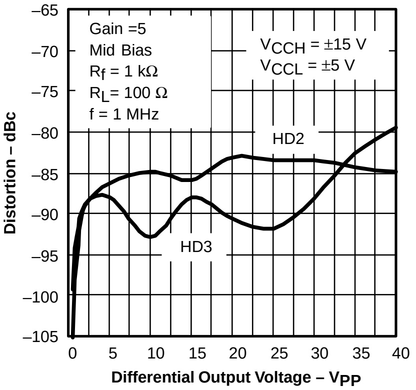


Figure 57

DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE

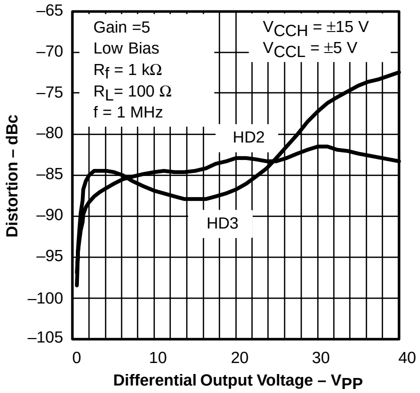


Figure 58

**DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE**

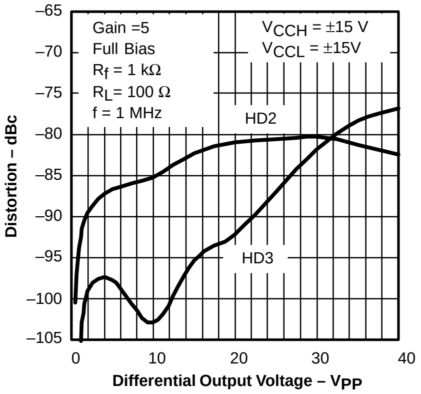


Figure 59

**DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE**

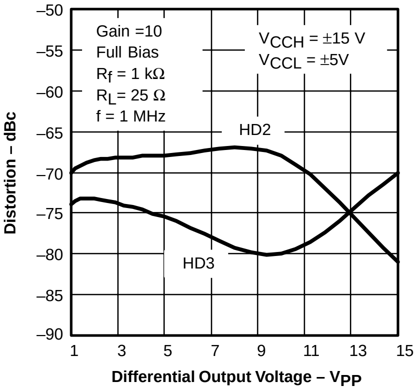


Figure 60

**DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE**

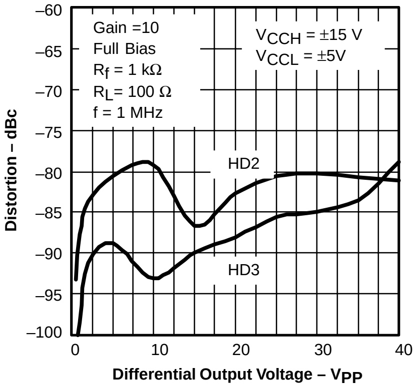


Figure 61

**DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE**

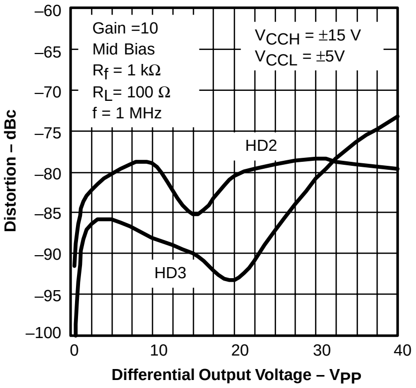


Figure 62

**DIFFERENTIAL DISTORTION
vs
DIFFERENTIAL OUTPUT VOLTAGE**

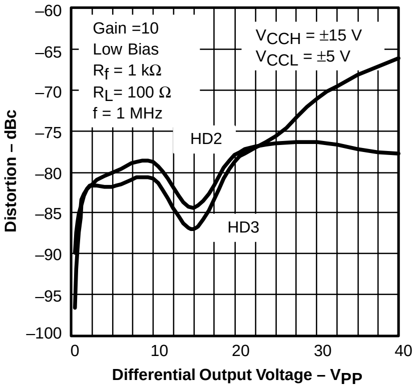


Figure 63

**SINGLE ENDED DISTORTION
vs
FREQUENCY**

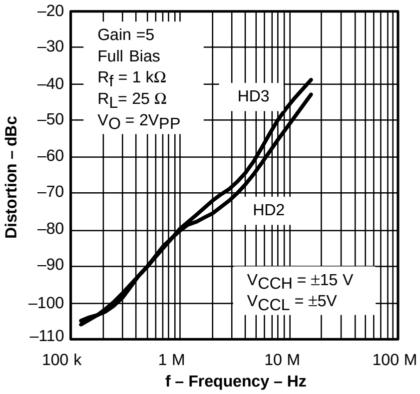


Figure 64

**SINGLE ENDED DISTORTION
vs
FREQUENCY**

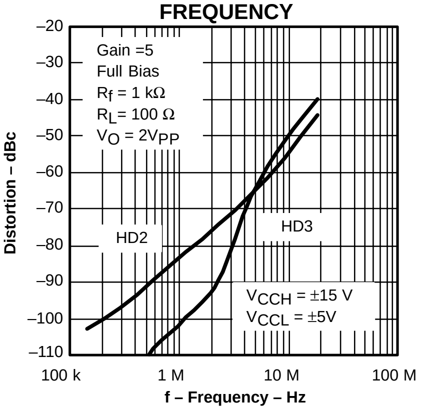
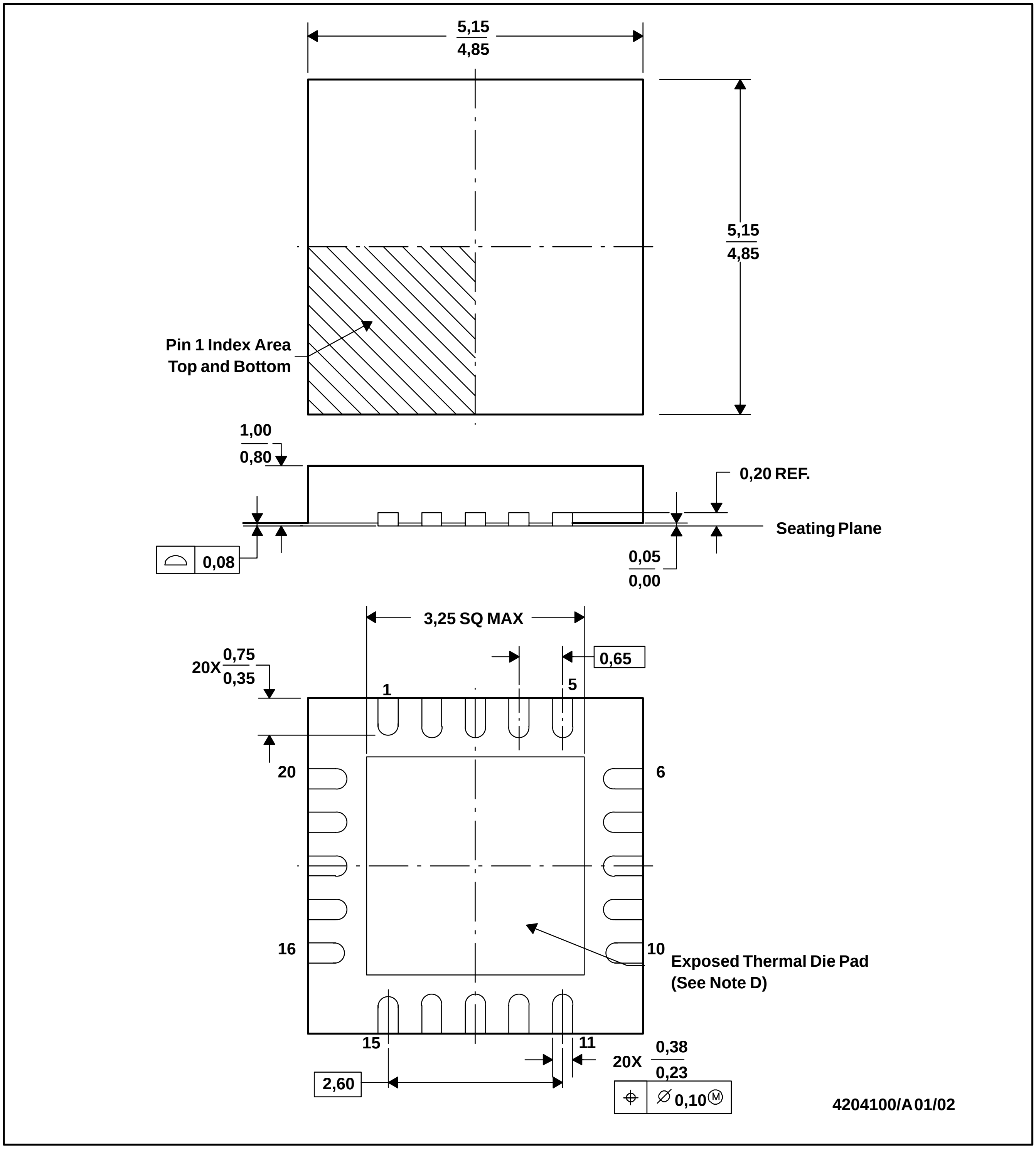


Figure 65

MECHANICAL DATA

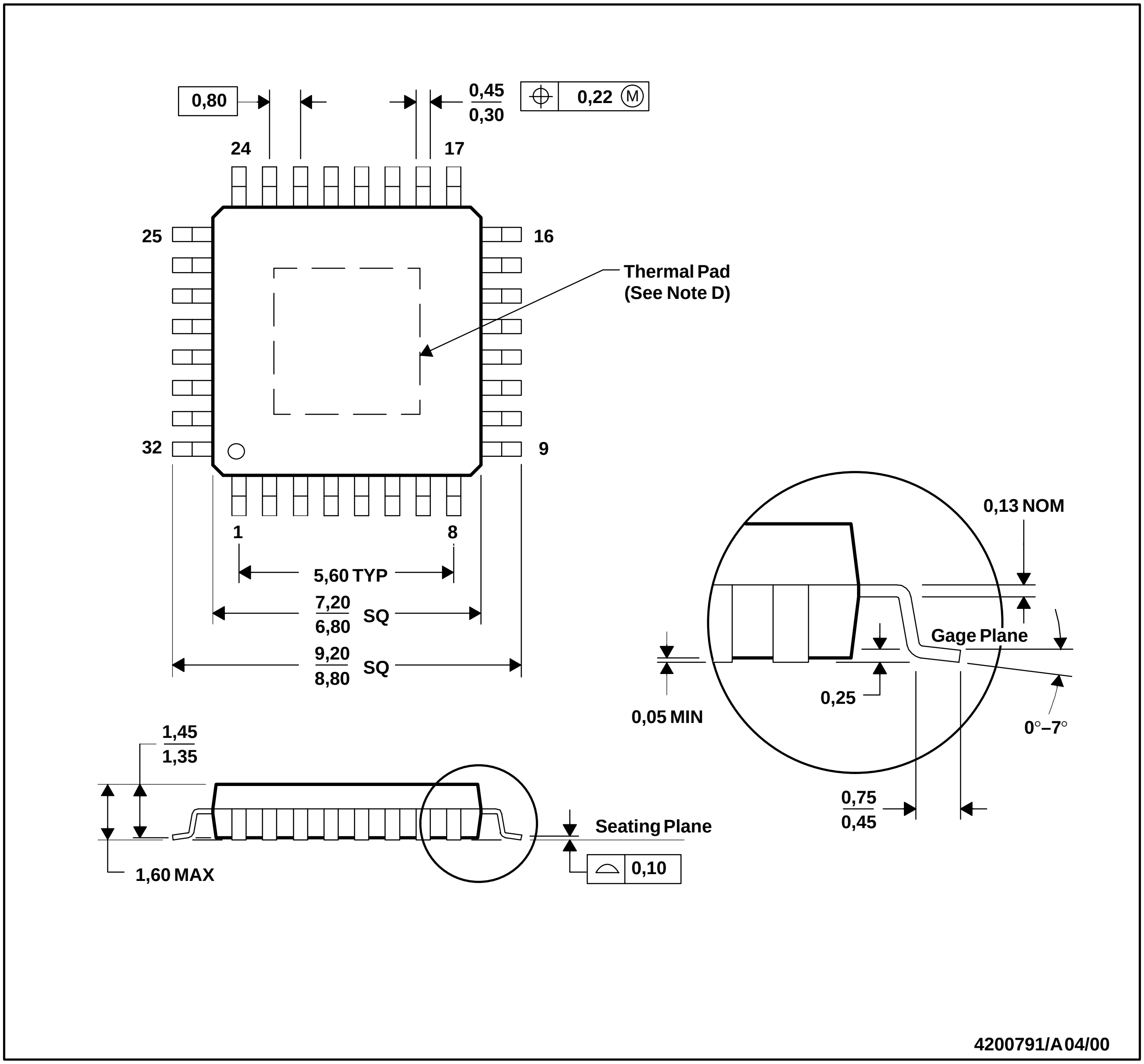
RGW (S-PQFP-N20) **PLASTIC QUAD FLATPACK**



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-leads, (QFN) package configuration.
- D. The package thermal performance may be enhanced by bonding the thermal die pad to an external thermal plane.
- E. Falls within JEDEC M0-220.

MECHANICAL DATA

VFP (S-PQFP-G32) **PowerPAD™ PLASTIC QUAD FLATPACK**



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. The package thermal performance may be enhanced by bonding the thermal pad to an external thermal plane. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.
- E. Falls within JEDEC MS-026

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